Abstract

There is provided a semiconductor device capable of improving the performance and reliability of a device. The semiconductor device including an active pattern extending in a first direction, a gate structure on the active pattern, the gate structure extending in a second direction different from the first direction and including a gate insulating layer and a gate filling layer, a gate spacer extending in the second direction, on a sidewall of the gate structure, a gate shield insulating pattern on a sidewall of the gate spacer, covering an upper surface of the gate insulating layer, and including an insulating material, and a gate capping pattern covering an upper surface of the gate filling layer, on the gate structure may be provided.

FIG. 4